Silicon Carbide Schottky Diode

650 V, 30 A

Description

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size and cost.

Features

- Max Junction Temperature 175°C
- Avalanche Rated 81 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery / No Forward Recovery

Applications

- General Purpose
- SMPS, Solar Inverter, UPS
- Power Switching Circuits

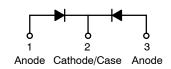


ON Semiconductor®

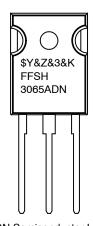
www.onsemi.com



TO-247 LONG LEAD CASE 340CH



MARKING DIAGRAM



\$Y = ON Semiconductor Logo &Z = Assembly Plant Code &3 = Numeric Date Code

&K = Lot Code

FFSH3065ADN = Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

Table 1. ABSOLUTE MAXIMUM RATINGS ($T_C = 25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	FFSH3065ADN-F155	Unit	
V_{RRM}	Peak Repetitive Reverse Voltage	650	V	
E _{AS}	Single Pulse Avalanche Energy (Note 1)		81	mJ
I _F	Continuous Rectified Forward Current @ T _C < 114°C		16*/30**	Α
	Continuous Rectified Forward Current @ T _C <	23**/36**		
I _{F,Max}	Non-Repetitive Peak Forward Surge Current	T _C = 25°C, 10 μs	1000	Α
		T _C = 150°C, 10 μs	900	Α
I _{F,SM}	Non-Repetitive Forward Surge Current	Half-Sine Pulse, t _p = 8.3 ms	90	Α
I _{F,RM}	Repetitive Forward Surge Current	Half-Sine Pulse, t _p = 8.3 ms	50	Α
Ptot	Power Dissipation	T _C = 25°C	165	W
		T _C = 150°C	28	W
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +175	°C
	TO247 Mounting Torque, M3 Screw	60	Ncm	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. E_{AS} of 81 mJ is based on starting $T_J = 25^{\circ}C$, L = 0.5 mH, $I_{AS} = 18$ A, V = 50 V.

Table 2. THERMAL CHARACTERISTICS

Symbol	Parameter	Rating	Unit
$R_{ heta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.91*/0.4**	°C/W

^{*} Per Leg

Table 3. OPERATING CHARACTERISTICS (T_C = 25°C, unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
V _F	Forward Voltage	I _F = 16 A, T _C = 25°C	-	1.5	1.75	V
		I _F = 16 A, T _C = 125°C	-	1.6	2.0	1
		I _F = 16 A, T _C = 175°C	-	1.72	2.4	1
I _R	Reverse Current	V _R = 650 V, T _C = 25°C	-	-	200	μΑ
		$V_R = 650 \text{ V}, T_C = 125^{\circ}\text{C}$	-	_	400	
		$V_R = 650 \text{ V}, T_C = 175^{\circ}\text{C}$	-	_	600	
Q _C	Total Capacitive Charge	V = 400 V	-	52	-	nC
С	Total Capacitance	V _R = 1 V, f = 100 kHz	-	887	_	pF
		V _R = 200 V, f = 100 kHz	-	95	_	
		V _R = 400 V, f = 100 kHz	-	72	-	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

PART MARKING AND ORDERING INFORMATION

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FFSH3065ADN-F155	FFSH3065ADN	TO-247 Long Lead	Tube	N/A	N/A	30 units

^{**} Per Device

TYPICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

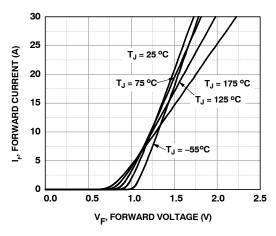
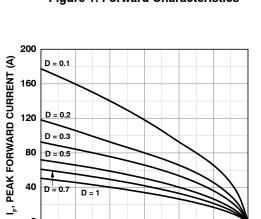


Figure 1. Forward Characteristics



 T_c , CASE TEMPERATURE (°C) Figure 3. Current Derating

100

125

150

175

75

50

25

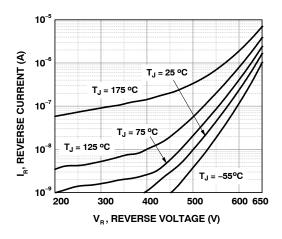


Figure 2. Reverse Characteristics

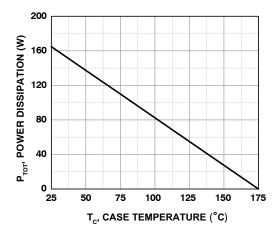


Figure 4. Power Derating

TYPICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

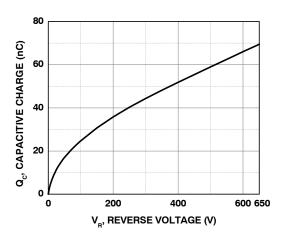


Figure 5. Capacitive Charge vs. Reverse Voltage

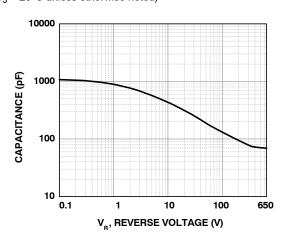


Figure 6. Capacitance vs. Reverse Voltage

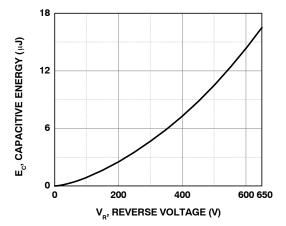


Figure 7. Capacitance Stored Energy

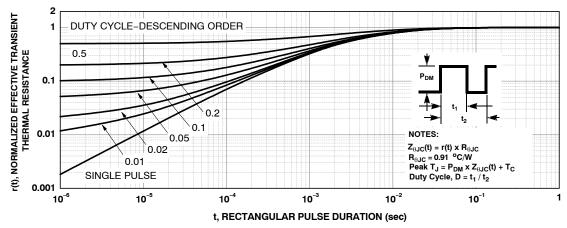


Figure 8. Junction-to-Case Transient Thermal Response Curve

$\textbf{TYPICAL CHARACTERISTICS} \ (T_J = 25^{\circ}\text{C unless otherwise noted})$

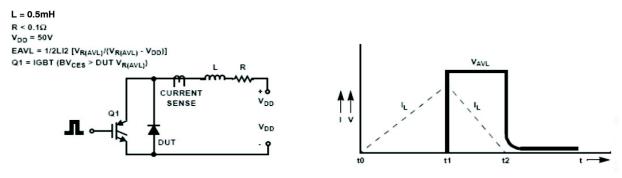
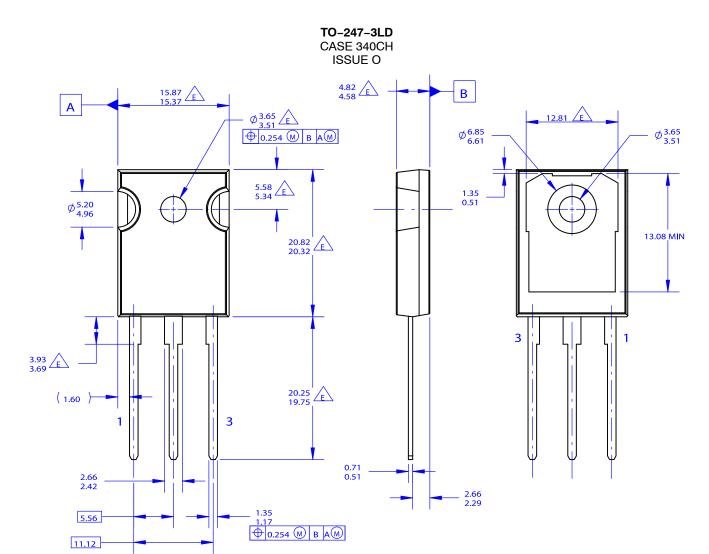


Figure 9. Unclamped Inductive Switching Test Circuit & Waveform

PACKAGE DIMENSIONS



NOTES: UNLESS OTHERWISE SPECIFIED.

- A. PACKAGE REFERENCE: JEDEC TO-247, ISSUE E, VARIATION AB, DATED JUNE, 2004.
- B. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- C. ALL DIMENSIONS ARE IN MILLIMETERS.
 D. DRAWING CONFORMS TO ASME Y14.5 1994

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